

B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

May 2023 Semester End Make-Up Examinations

Programme: B.E.

Branch: Electronics and Communication Engineering

Course Code: 16EC5DCMWE

Course: Microwave Engineering

Semester: V

Duration: 3 hrs.

Max Marks: 100

Date: 17.05.2023

Instructions: 1. Answer any FIVE full questions, choosing one full question from each unit.
2. Missing data, if any, may be suitably assumed.

UNIT - I

- 1 a) Why transmission lines are called distributed parameter networks? Derive the expression for voltage $V(z)$ and current $I(z)$ on a uniform transmission line considering lumped equivalent circuit of a small section of a uniform transmission line. **10**
- b) Explain in brief reflection coefficient, Transmission coefficient and Standing wave ratio with respect to a transmission line. Derive the relation between them. **10**

UNIT - II

- 2 a) State and prove properties of scattering matrix. **12**
- b) S-parameters of a two-port network are given by **08**

$$[S] = \begin{bmatrix} 0.1 \angle 0^\circ & 0.9 \angle 45^\circ \\ 0.9 \angle 45^\circ & 0.3 \angle 45^\circ \end{bmatrix}$$

Determine whether network is (i) Reciprocal (ii) Lossless

What is the return loss at port 1 when port 2 is short circuited.

UNIT - III

- 3 a) Explain construction and operation of a Magic-Tee with neat diagram. Obtain it's S-matrix. Explain any one application of Magic-Tee. **10**
- b) A 3-port circulator has an insertion loss of 1dB and an isolation of 30dB. If VSWR=1.5, Obtain it's S-matrix. **10**

OR

- 4 a) What is a circulator? Explain any one way of obtaining a 4-port circulator. Write it's S-matrix. **10**
- b) Show that if a pair of ports of a 4-port lossless reciprocal Junction are de-coupled, the other pair of ports are also de-coupled. **10**

UNIT - IV

- 5 a) Explain the construction and operation of PIN diode. Compare PIN diode with ordinary PN junction diode. With neat diagram, explain how a PIN diode is used as RF Switch. **10**
- b) With neat diagrams, describe the construction of any one form of IMPATT diode. Explain its operation with relevant waveforms. **08**
- c) An IMPATT diode has a drift length of 2 micro meter. Determine the operating frequency of IMPATT diode if the drift velocity for Si is 10^7 cm/sec. **02**

OR

- 6 a) With neat diagrams, explain the working of Reflex Klystron Oscillator. A Reflex Klystron is to be operated at 10GHz with a beam voltage of 300V, Repeller space of 0.1 cm, and $1\frac{3}{4}$ mode. Calculate PRFmax and corresponding repeller voltage for a beam current of 20 mA. **12**
- b) With neat diagram explain the working of a negative resistance Parametric Amplifier. Compare negative resistance Parametric amplifier and Parametric Up-converter. **08**

UNIT - V

- 7 a) Explain what you understand by EMI and EMC and why it is important in RF design. **10**
- b) Describe how microwaves are utilized in medical field and explain the effect of Microwaves on human body. **10**
